ABSTRACT OF THE DISCLOSURE

A semiconductor laser device has an active layer, a first cladding layer formed on the active layer, and a second cladding layer formed on the first cladding layer. The first cladding layer is doped with magnesium as a first impurity to have a high resistivity. The second cladding layer is doped with zinc as a second impurity to have a resistivity lower than the resistivity of the first cladding layer.

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